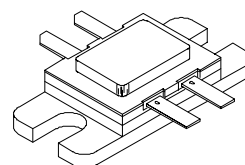


## RF & MICROWAVE TRANSISTORS UHF PULSED APPLICATIONS

- 500 WATTS @ 250μSec PULSE WIDTH, 10% DUTY CYCLE
- REFRACTORY GOLD METALLIZATION
- EMITTER BALLASTING AND LOW RESISTANCE FOR RELIABILITY AND RUGGEDNESS
- INFINITE VSWR CAPABILITY AT SPECIFIED OPERATING CONDITIONS
- INPUT MATCHED, COMMON BASE CONFIGURATION
- BALANCED CONFIGURATION



**.400 x .500 4LFL (M102)**

hermetically sealed

**ORDER CODE**

SD1565

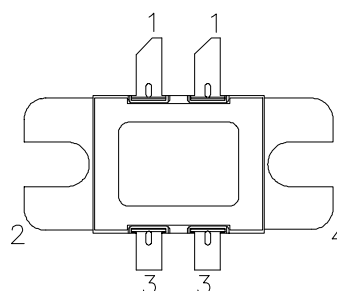
**BRANDING**

SD1565

### DESCRIPTION

The SD1565 is a hermetically sealed, gold metallized silicon NPN pulse power transistor mounted in a common base balanced configuration. The SD1565 is designed for applications requiring high peak power and low duty cycles within the frequency range of 400 - 500 MHz.

### PIN CONNECTION



- |              |            |
|--------------|------------|
| 1. Collector | 3. Emitter |
| 2. Base      | 4. Base    |

### ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	65	V
V <sub>CES</sub>	Collector-Emitter Voltage	65	V
V <sub>EBO</sub>	Emitter-Base Voltage	3.5	V
I <sub>C</sub>	Device Current	43.2	A
P <sub>DISS</sub>	Power Dissipation	1167	W
T <sub>J</sub>	Junction Temperature	+200	°C
T <sub>STG</sub>	Storage Temperature	- 65 to +200	°C

### THERMAL DATA

R <sub>TH(j-c)</sub>	Junction-Case Thermal Resistance	0.15	°C/W
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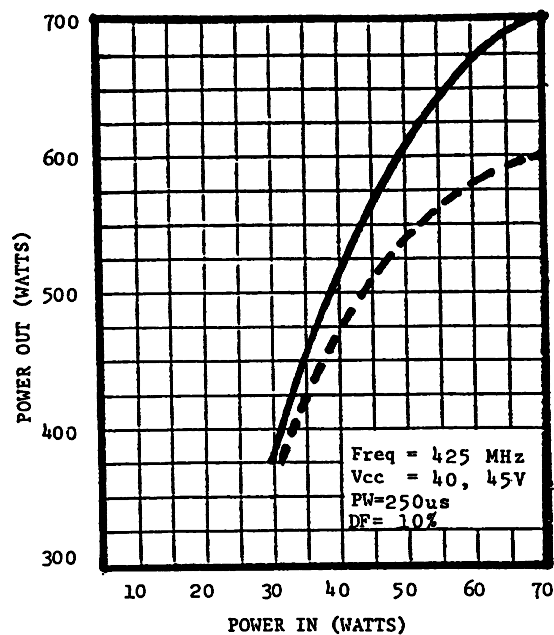
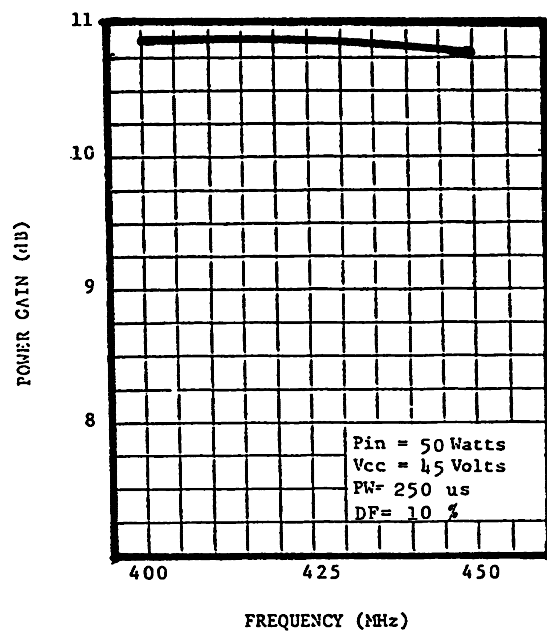
**ELECTRICAL SPECIFICATIONS** ( $T_{case} = 25^{\circ}C$ )**STATIC**

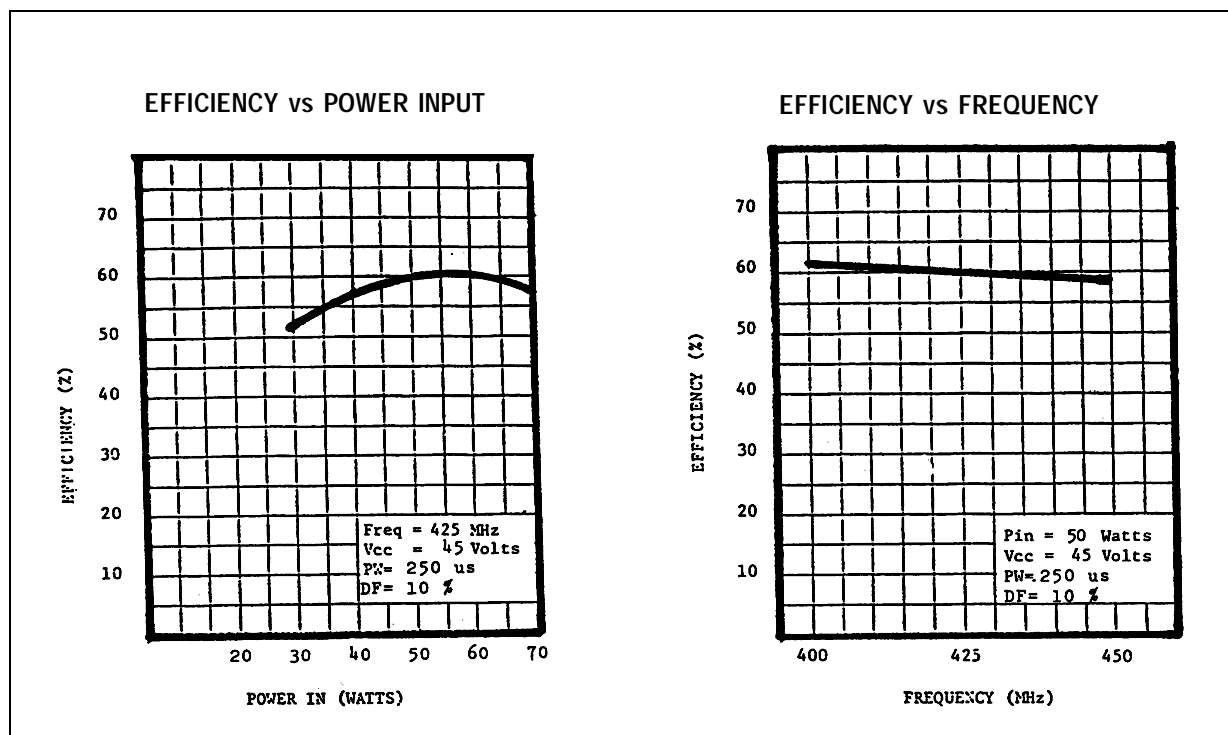
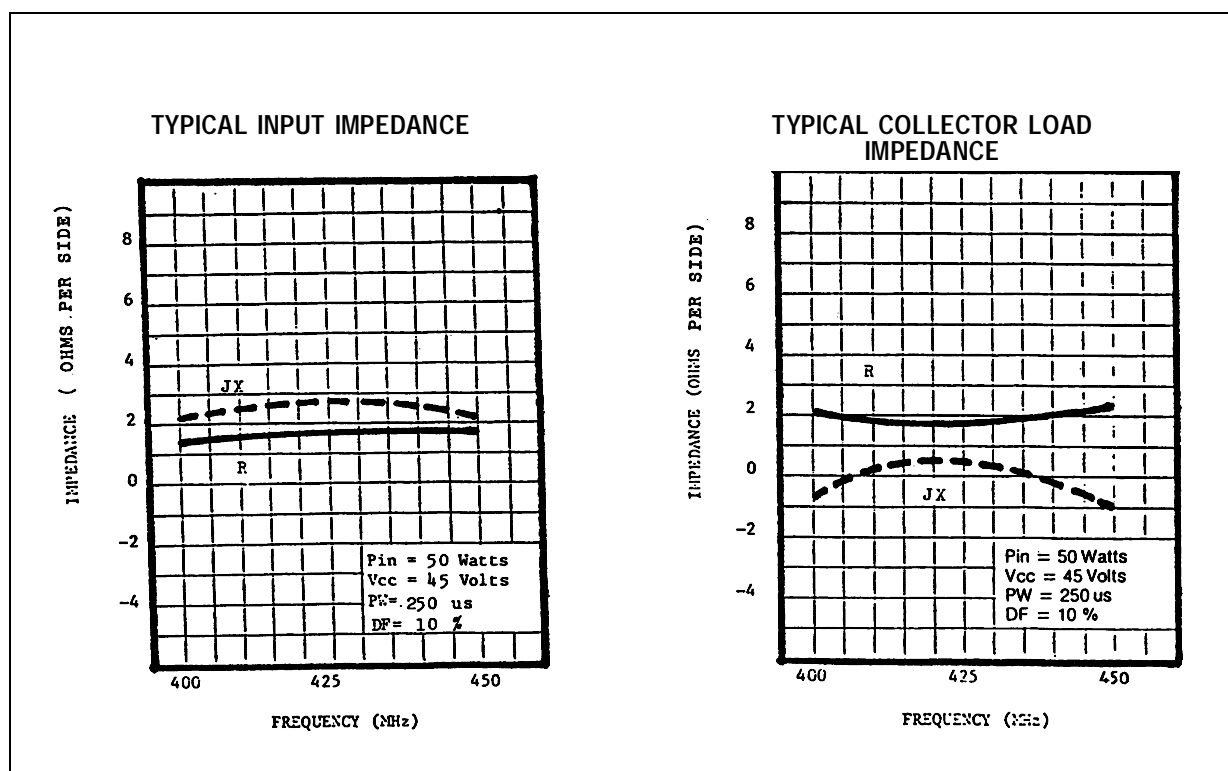
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
$BV_{CBO}$	$I_C = 50\text{ mA}$	$I_E = 0\text{ mA}$	65	—	—	V
$BV_{CES}$	$I_C = 50\text{ mA}$	$V_{BE} = 0\text{ V}$	65	—	—	V
$BV_{EBO}$	$I_E = 10\text{ mA}$	$I_C = 0\text{ mA}$	3.5	—	—	V
$I_{CES}$	$V_{CE} = 30\text{ V}$	$I_E = 0\text{ mA}$	—	—	15	mA
$h_{FE}$	$V_{CE} = 5\text{ V}$	$I_C = 5\text{ A}$	20	—	200	—

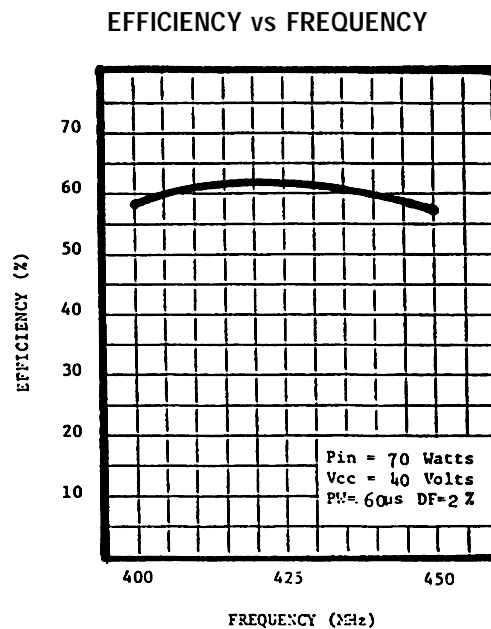
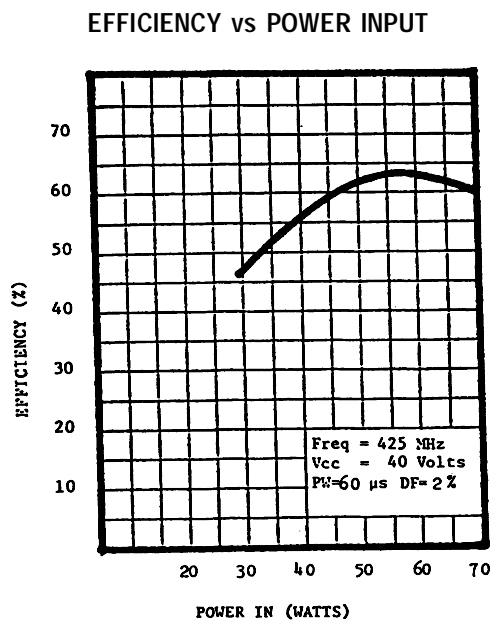
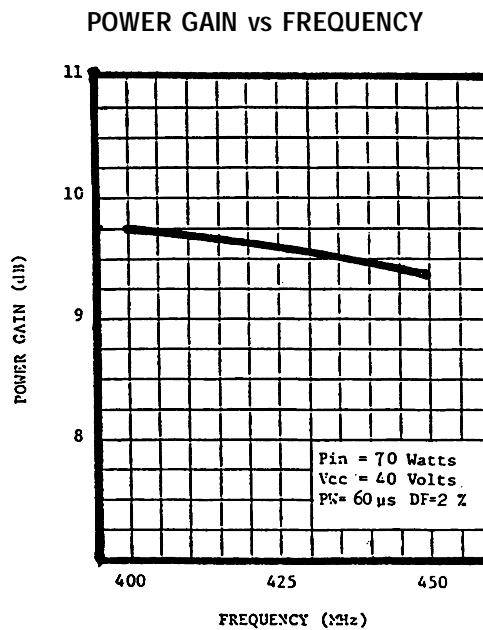
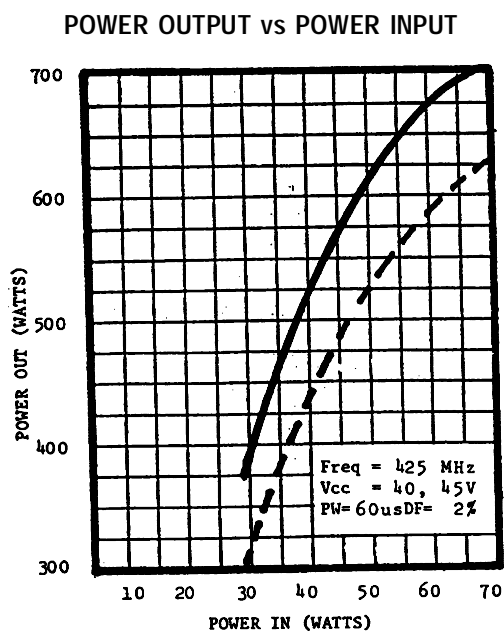
**DYNAMIC**

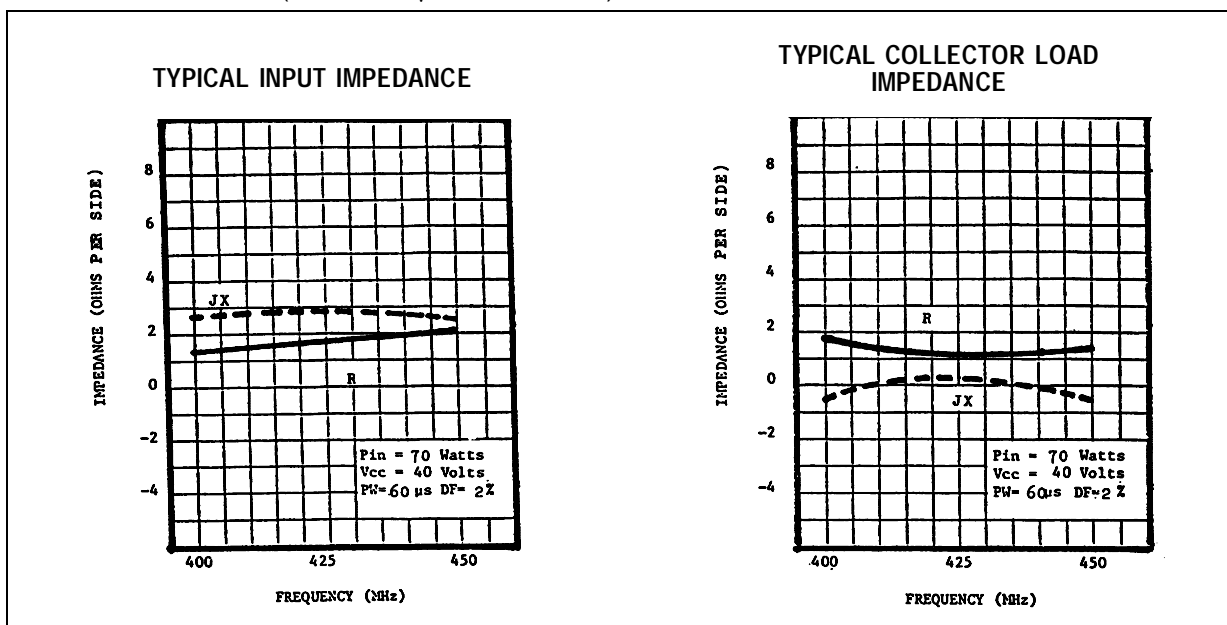
Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
$P_{OUT}$	$f = 425\text{ MHz}$	$P_{IN} = 54\text{ W}$	$V_{CE} = 40\text{ V}$	500	—	—	W
$P_G$	$f = 425\text{ MHz}$	$P_{IN} = 54\text{ W}$	$V_{CE} = 40\text{ V}$	9.7	—	—	dB
$\eta_c$	$f = 425\text{ MHz}$	$P_{IN} = 54\text{ W}$	$V_{CE} = 40\text{ V}$	50	—	—	%

Note: Pulse Width = 250 $\mu$ Sec, Duty Cycle = 10%  
 This device is suitable for use under other pulse width/duty cycle conditions.  
 Please contact the factory for specific applications assistance.

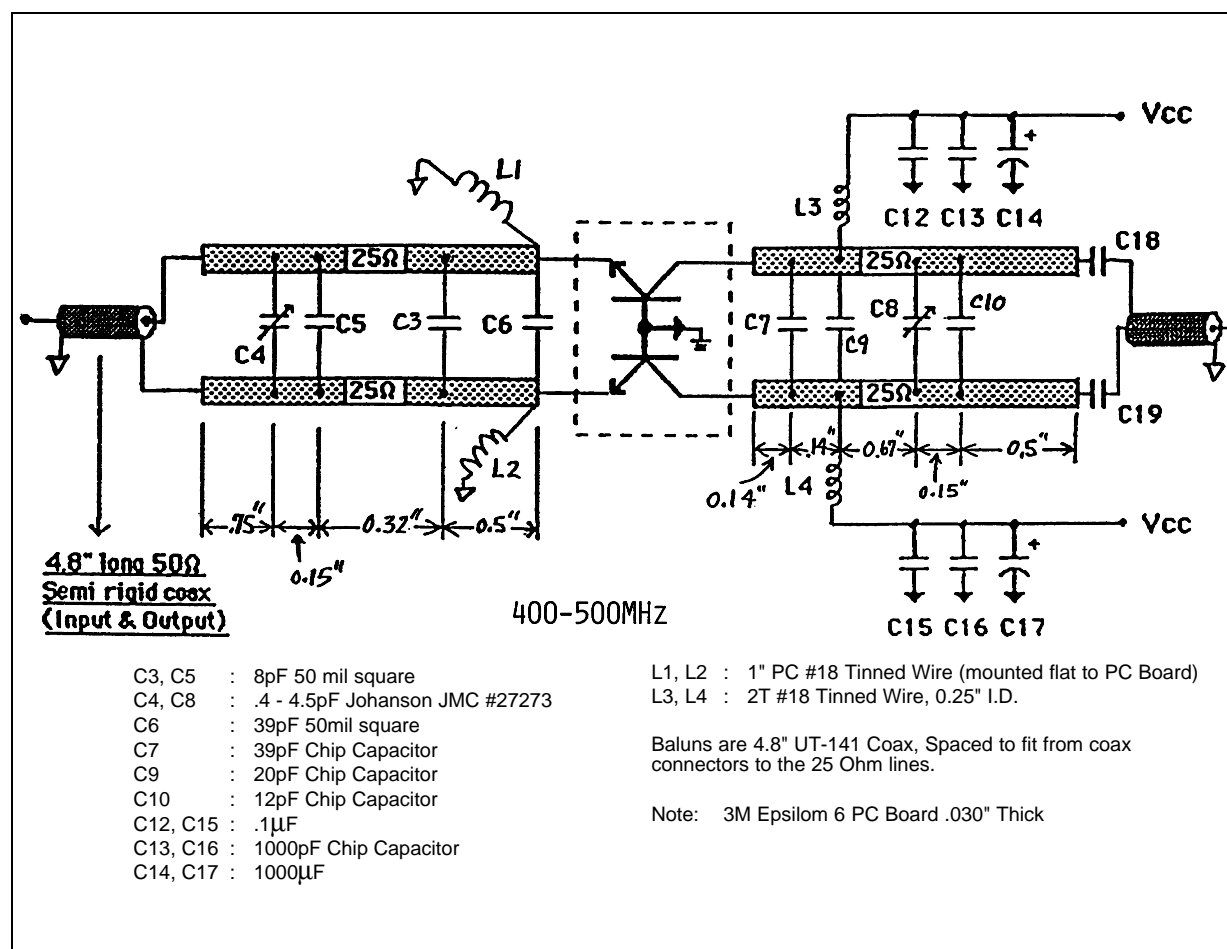
**TYPICAL PERFORMANCE** (P.W. = 250 $\mu$ S, D.C. = 10%)**POWER OUTPUT vs POWER INPUT****POWER GAIN vs FREQUENCY**

TYPICAL PERFORMANCE (P.W. = 250 $\mu$ S, D.C. = 10%)IMPEDANCE DATA (P.W. = 250 $\mu$ S, D.C. = 10%)

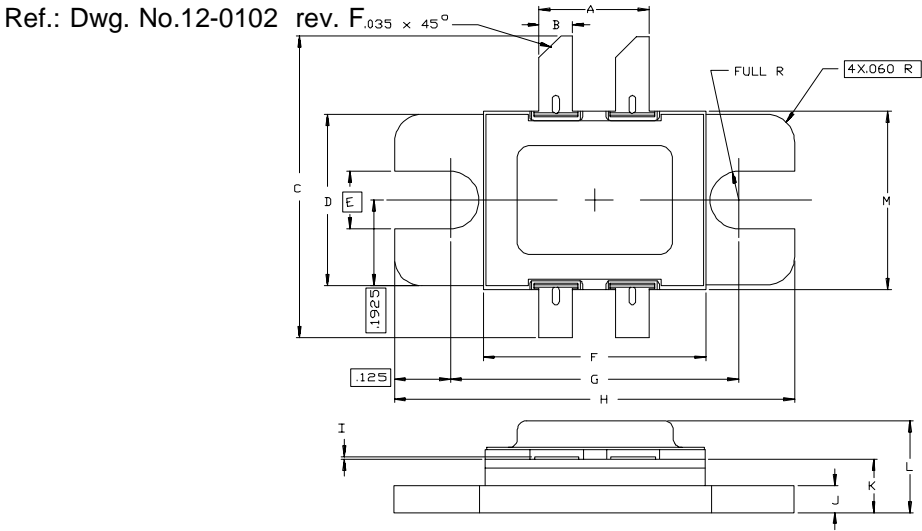
TYPICAL PERFORMANCE (P.W. = 60 $\mu$ S, D.C. = 2%)

IMPEDANCE DATA (P.W. = 60 $\mu$ S, D.C. = 2%)

## TEST CIRCUIT



PACKAGE MECHANICAL DATA



SGS-THOMSON MICROELECTRONICS			CONT'D		
	MINIMUM Inches/mm	MAXIMUM Inches/mm		MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.240/6,10	.254/6,45	K	.115/2,92	.130/3,30
B	.070/1,78	.080/2,03	L	---	.230/5,84
C	.780/19,81	.820/20,83	M	.395/10,03	.407/10,34
D	.380/9,65	.390/9,91			
E	.130/3,30				
F	.495/12,57	.507/12,88			
G	.640/16,26	.655/16,64			
H	.890/22,61	.910/23,11			
I	.002/0,05	.006/0,15			
J	.058/1,47	.065/1,65			

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